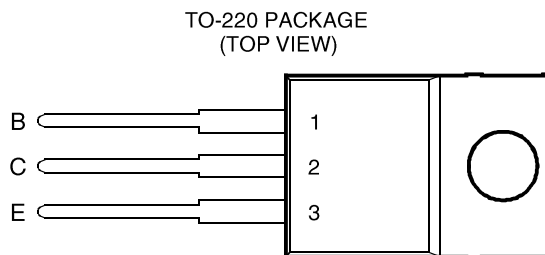


- **Designed for Complementary Use with the BD242 Series**
- **40 W at 25°C Case Temperature**
- **3 A Continuous Collector Current**
- **5 A Peak Collector Current**
- **Customer-Specified Selections Available**



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings **at 25°C case temperature (unless otherwise noted)**

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage ( $R_{BE} = 100 \Omega$ )	BD241	$V_{CEr}$	55	V
	BD241A		70	
	BD241B		90	
	BD241C		115	
Collector-emitter voltage ( $I_C = 30 \text{ mA}$ )	BD241	$V_{CE0}$	45	V
	BD241A		60	
	BD241B		80	
	BD241C		100	
Emitter-base voltage		$V_{EBO}$	5	V
Continuous collector current		$I_C$	3	A
Peak collector current (see Note 1)		$I_{CM}$	5	A
Continuous base current		$I_B$	1	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		$P_{tot}$	40	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		$P_{tot}$	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	32	mJ
Operating junction temperature range		$T_j$	-65 to +150	°C
Storage temperature range		$T_{stg}$	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		$T_L$	250	°C

NOTES: 1. This value applies for  $t_p \leq 0.3 \text{ ms}$ , duty cycle  $\leq 10\%$ .

2. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of:  $L = 20 \text{ mH}$ ,  $I_{B(on)} = 0.4 \text{ A}$ ,  $R_{BE} = 100 \Omega$ ,  $V_{BE(off)} = 0$ ,  $R_S = 0.1 \Omega$ ,  $V_{CC} = 20 \text{ V}$ .

# BD241, BD241A, BD241B, BD241C

## NPN SILICON POWER TRANSISTORS

### electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5)	$I_B = 0$	BD241	45			V
			BD241A	60			
			BD241B	80			
			BD241C	100			
$I_{CES}$ Collector-emitter cut-off current	$V_{CE} = 55 \text{ V}$	$V_{BE} = 0$	BD241			0.2	mA
	$V_{CE} = 70 \text{ V}$	$V_{BE} = 0$	BD241A			0.2	
	$V_{CE} = 90 \text{ V}$	$V_{BE} = 0$	BD241B			0.2	
	$V_{CE} = 115 \text{ V}$	$V_{BE} = 0$	BD241C			0.2	
$I_{CEO}$ Collector cut-off current	$V_{CE} = 30 \text{ V}$	$I_B = 0$	BD241/241A			0.3	mA
	$V_{CE} = 60 \text{ V}$	$I_B = 0$	BD241B/241C			0.3	
$I_{EBO}$ Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				1	mA
$h_{FE}$ Forward current transfer ratio	$V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$	(see Notes 5 and 6)	25			
	$V_{CE} = 4 \text{ V}$	$I_C = 3 \text{ A}$		10			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 0.6 \text{ A}$	$I_C = 3 \text{ A}$	(see Notes 5 and 6)			1.2	V
$V_{BE}$ Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 3 \text{ A}$	(see Notes 5 and 6)			1.8	V
$h_{fe}$ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

### thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			3.125	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

### resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
$t_{on}$ Turn-on time	$I_C = 1 \text{ A}$	$I_{B(on)} = 0.1 \text{ A}$	$I_{B(off)} = -0.1 \text{ A}$		0.3		$\mu\text{s}$
$t_{off}$ Turn-off time	$V_{BE(off)} = -3.7 \text{ V}$	$R_L = 20 \Omega$	$t_p = 20 \mu\text{s}$ , dc $\leq 2\%$		1		$\mu\text{s}$

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

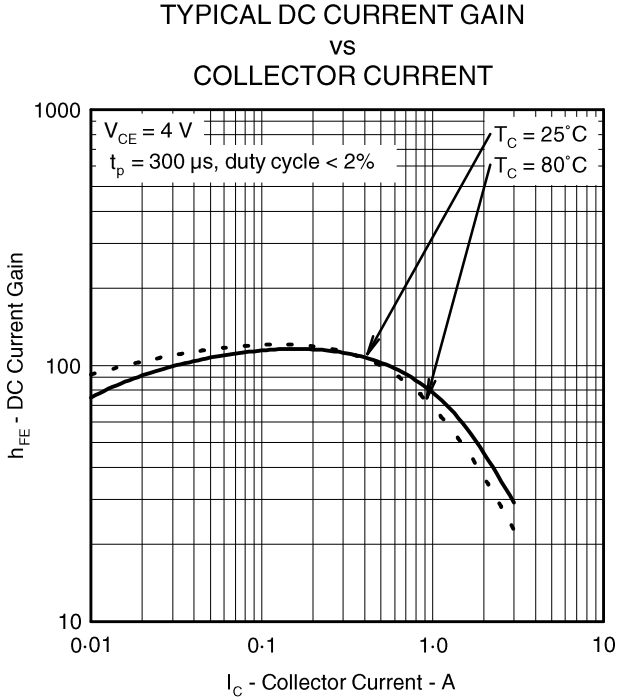


Figure 1.

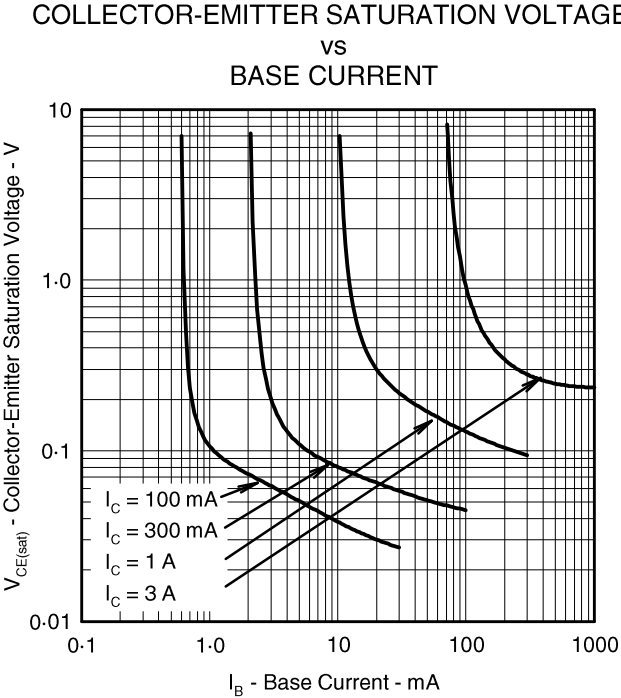


Figure 2.

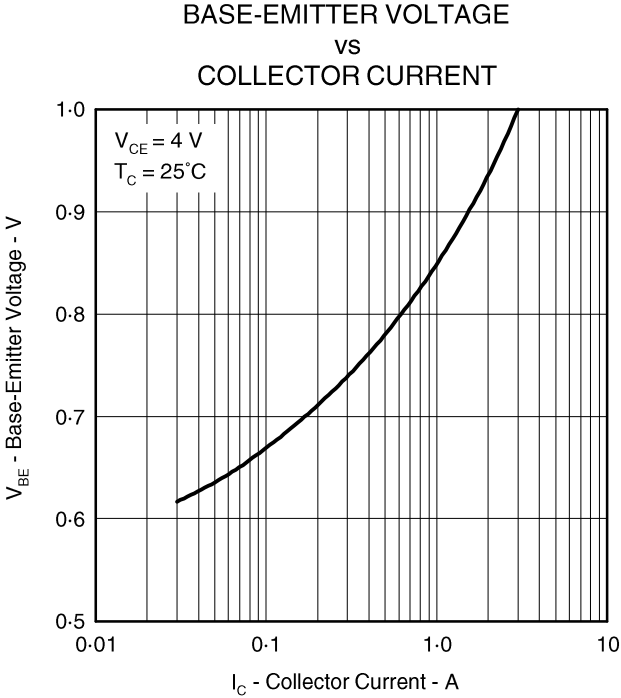


Figure 3.

**BD241, BD241A, BD241B, BD241C  
NPN SILICON POWER TRANSISTORS**

**MAXIMUM SAFE OPERATING REGIONS**

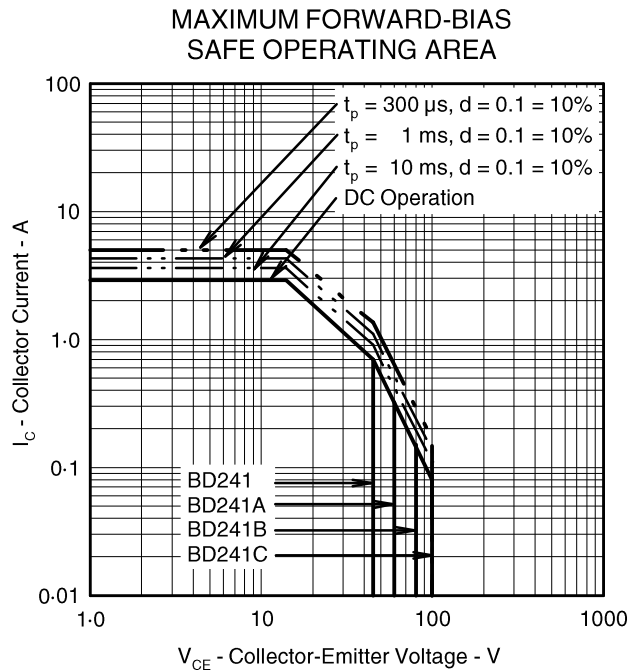


Figure 4.

**THERMAL INFORMATION**

**MAXIMUM POWER DISSIPATION  
vs  
CASE TEMPERATURE**

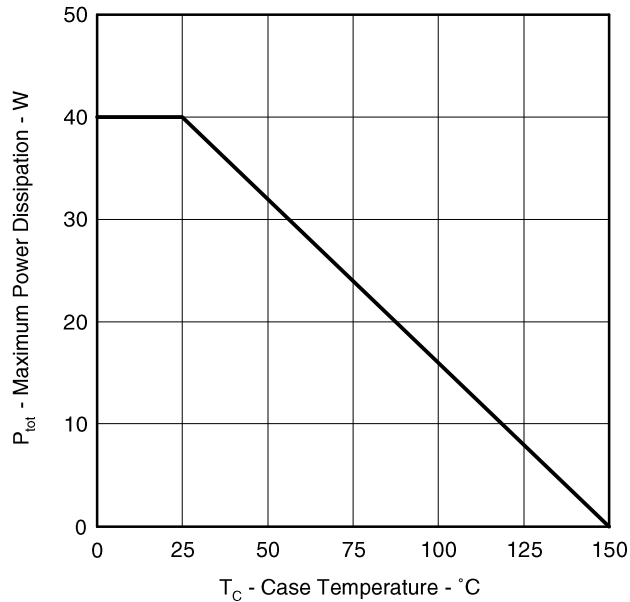


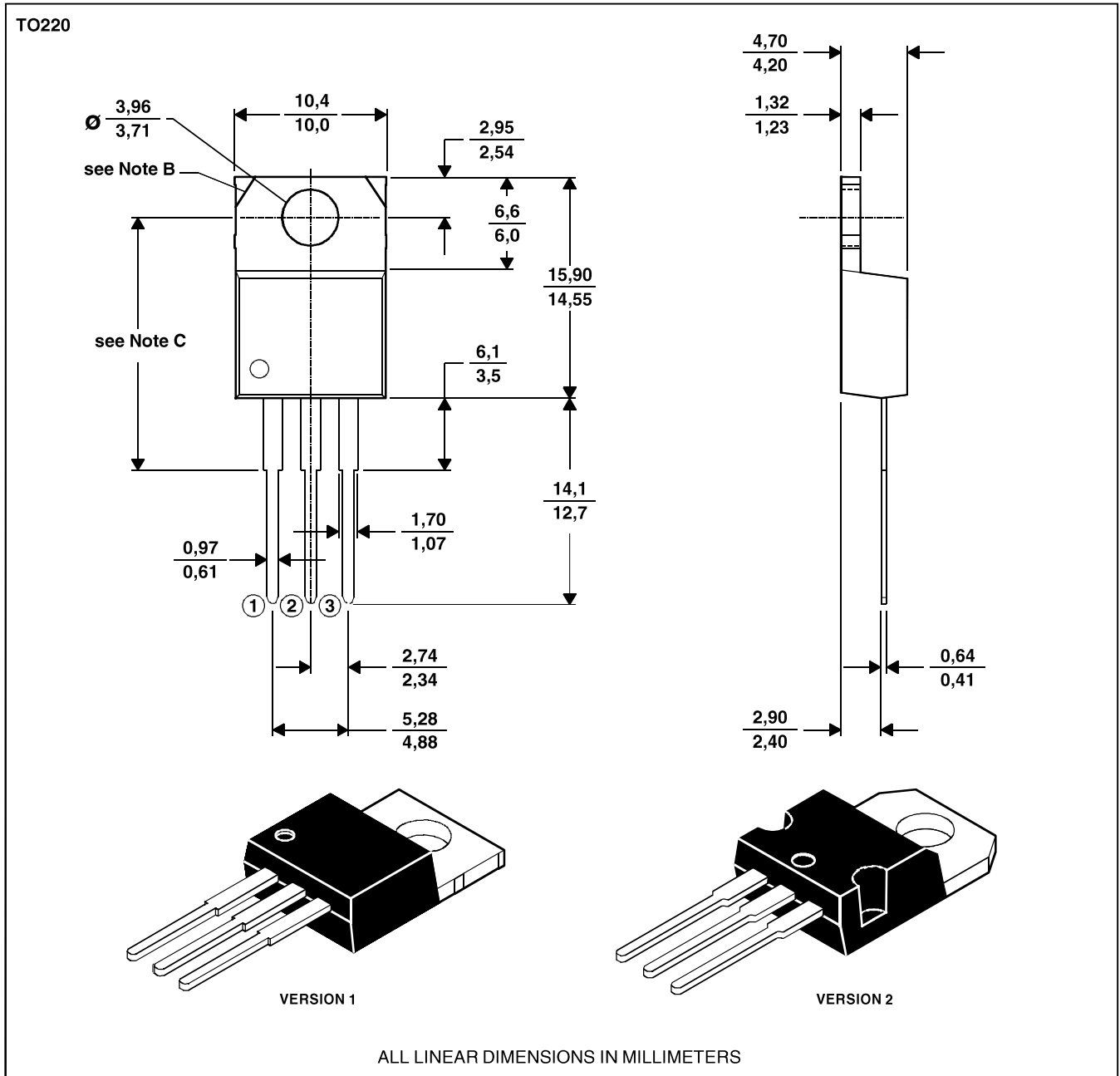
Figure 5.

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. The centre pin is in electrical contact with the mounting tab.  
 B. Mounting tab corner profile according to package version.  
 C. Typical fixing hole centre stand off height according to package version.  
 Version 1, 18.0 mm. Version 2, 17.6 mm.